

# Optimization of low-valence Ga PAWs for faster DFT calculations of point defects in GaN

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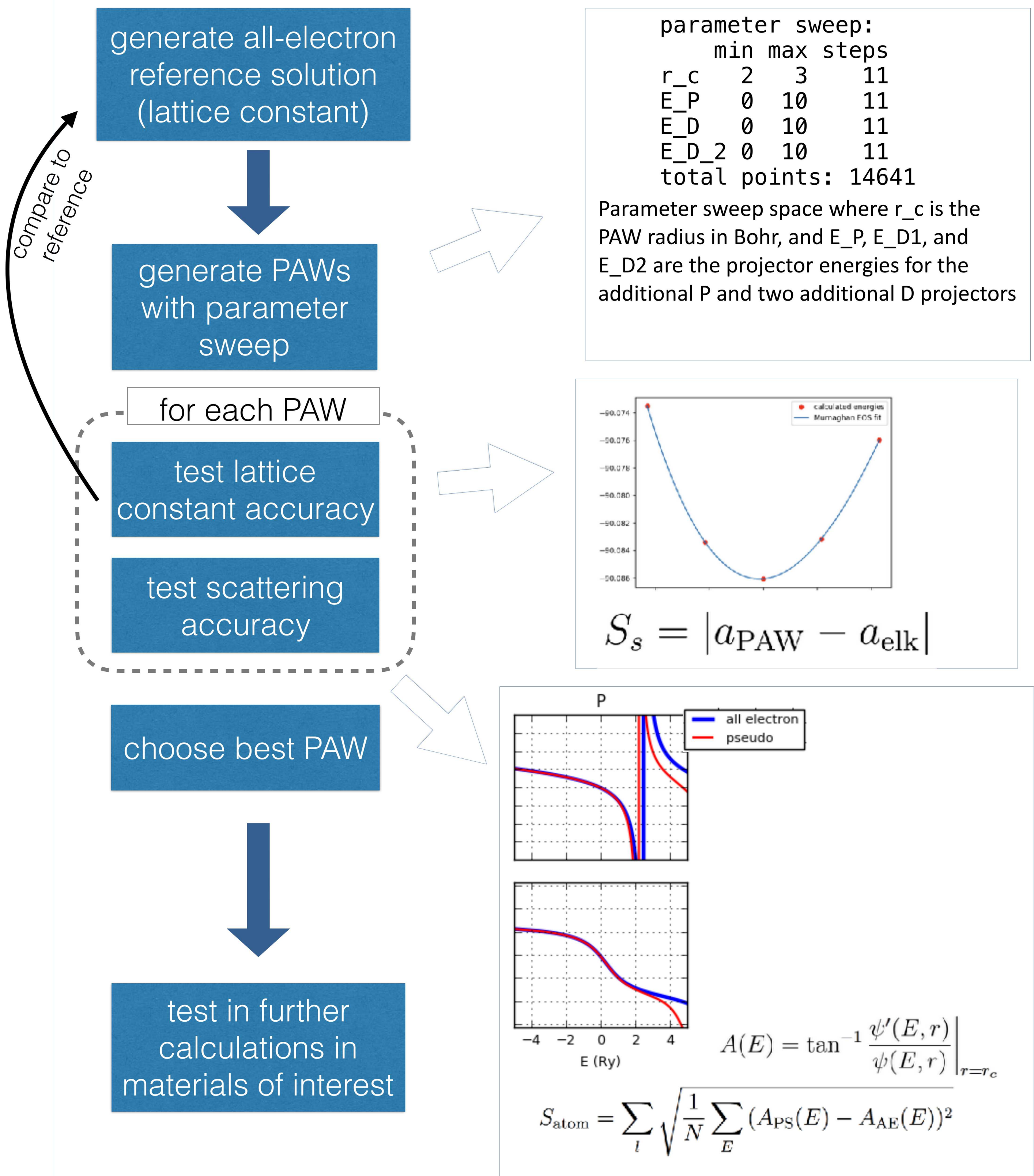
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## Introduction

- Want to study defects in gallium nitride (GaN) using plane-wave density functional theory (DFT) and projector augmented wave data sets (PAWs)
- However, for the large system sizes required for accurate defect studies, there is a strong need to reduce computational expense of the DFT calculations
- If quantum molecular dynamics (QMD) studies are required, existing Ga PAWs are too slow because of supercell sizes and time steps required
- Objective:** use optimization to tune parameters of a new 3-electron Ga PAW, evaluating scattering properties and zb-GaN lattice parameter for each PAW. Then, evaluate accuracy and speedup of new PAW in defect calculations in GaN to see if it speeds up the calculations without adversely affecting the results

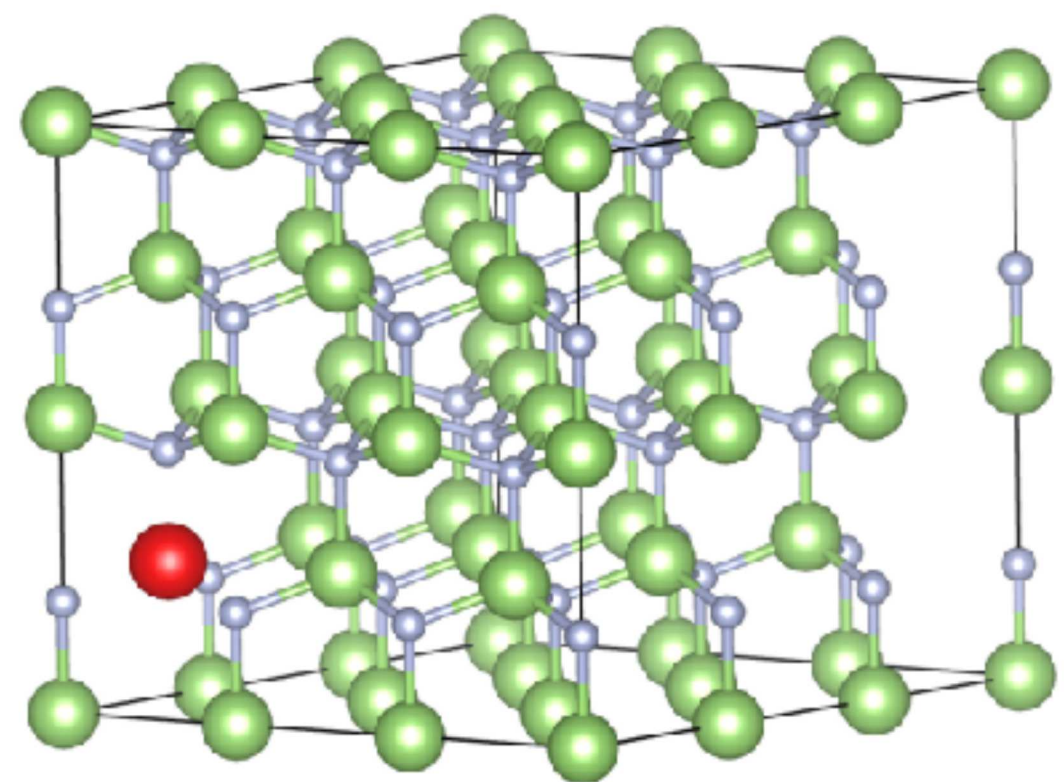
## Methods: PAW Optimizations



## Methods: Defect Calculations

### To get defect transition levels:

- remove Ga atom from unit cell
- relax structure
- calculate total energy
- repeat relaxation and total energy calculation for different charge states
- Calculate transition levels:  
 $E_L[q-1, q] = E[q-1] - E[q] - E_{\text{shift}}$   
where q is charge state and  $E_{\text{shift}}$  is *usually* the valence band edge
- the charge is no longer localized on the defect when the levels are at the bounds (red lines in results)

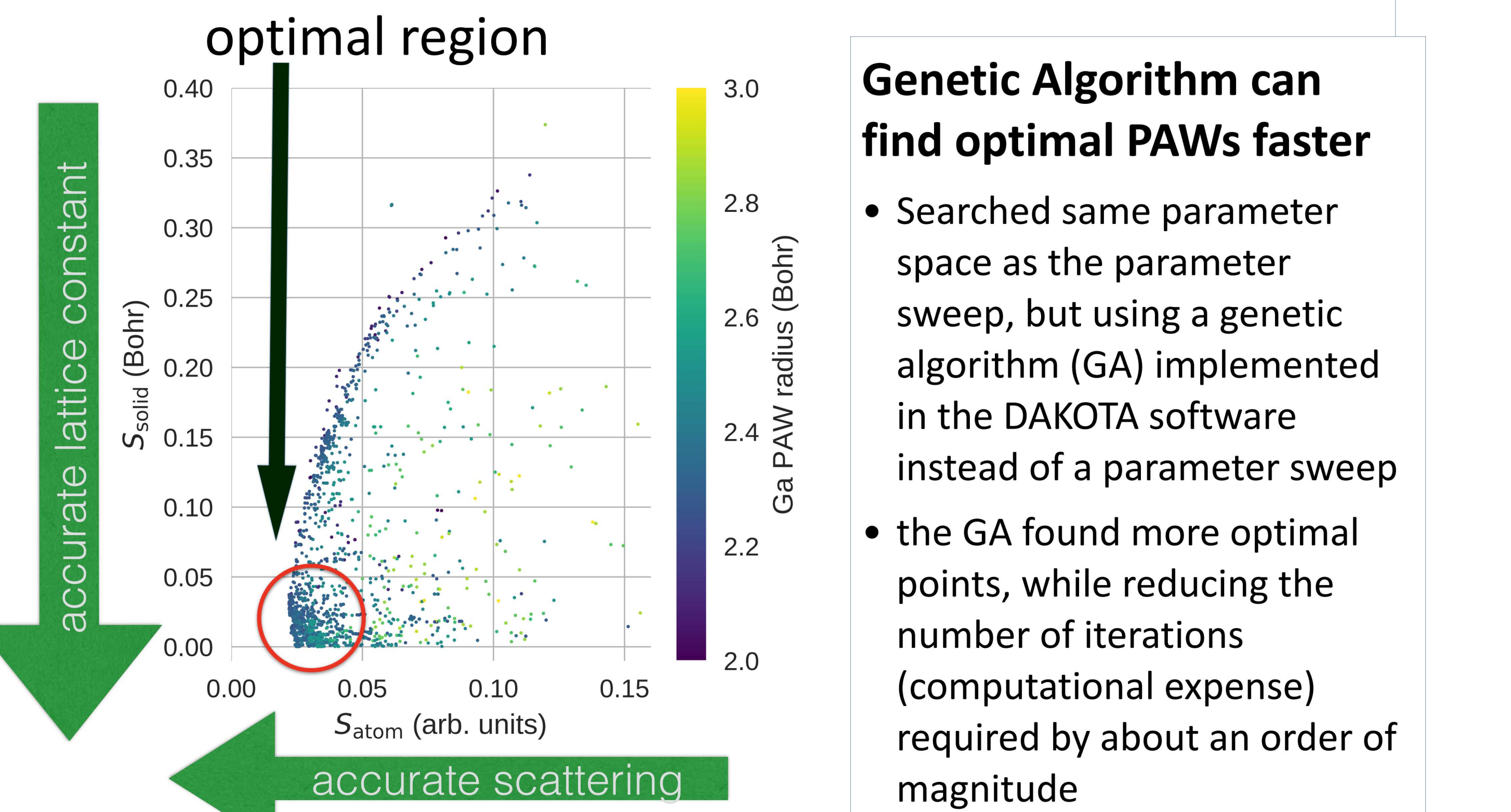
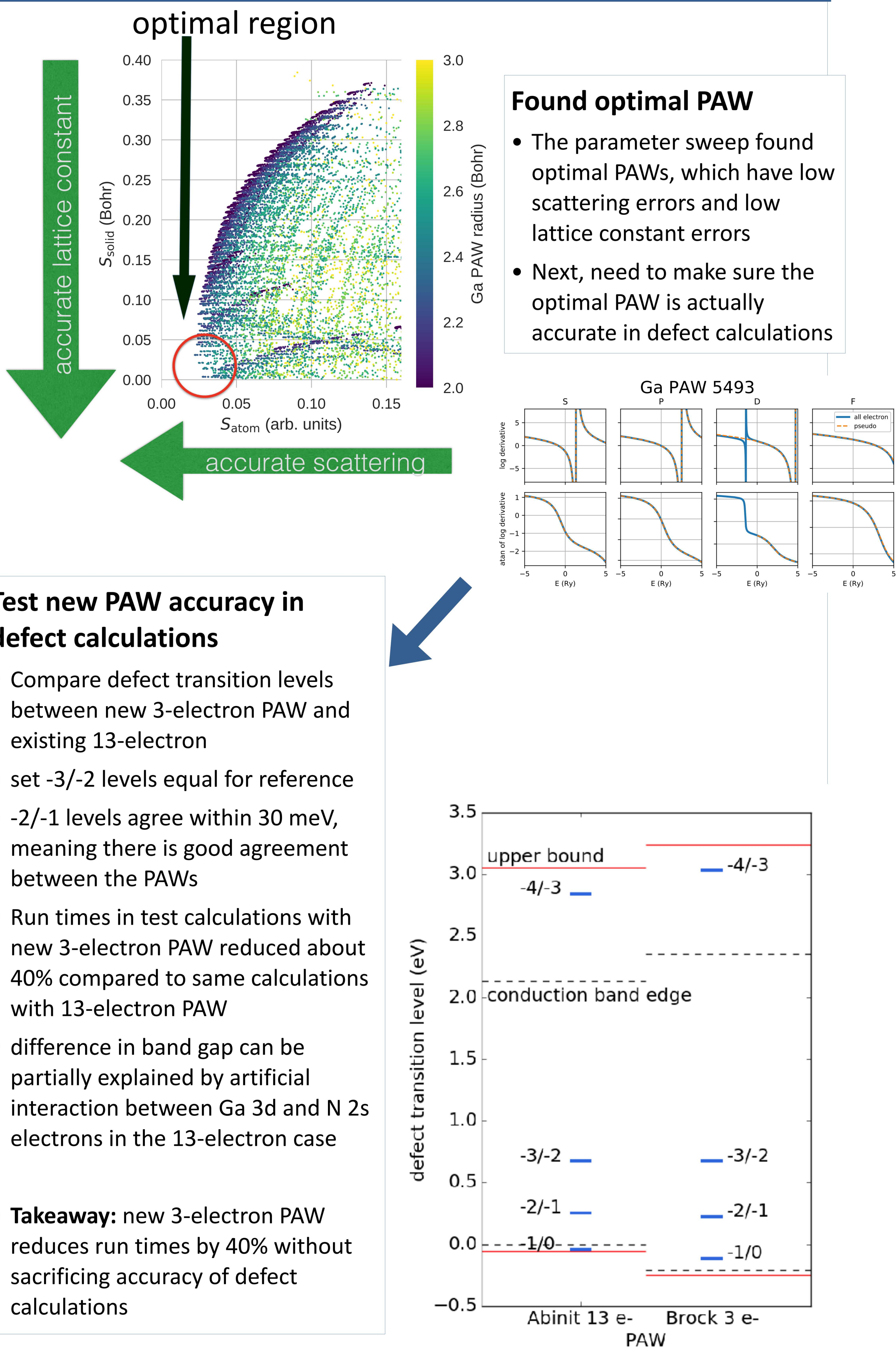


Ga vacancy in wurtzite GaN

### To get band gap and bounds:

- Band gap comes from neutral bulk structure with no defect
- The bounds are the energies required to add or remove an electron from the unit cell, *which are only equivalent to the band edges in an infinite size cell*

## Results



## Conclusions

- Generated a 3-electron Ga PAW that reduces computational expense of defect calculations in GaN by about 40%
- A genetic algorithm can improve optimization results over a parameter sweep with an order of magnitude fewer iterations
- This optimization process could be applied to other systems where custom PAWs would improve accuracy or speed of plane-wave DFT calculations

## Acknowledgements

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